

Amendments to the claims

1. (Original) A solid-state image-sensing device comprising:
a first pixel including a photoelectric conversion element and capable of generating an output signal that is logarithmically proportional to an amount of light incident on the photoelectric conversion element;
a second pixel for generating as an output signal a compensation signal with which to compensate the output signal of the first pixel; and
a reading circuit for reading out the output signals of the first and second pixels.
2. (Original) A solid-state image-sensing device as claimed in claim 1, wherein the solid-state image-sensing device has a plurality of first pixels.
3. (Original) A solid-state image-sensing device as claimed in claim 2, wherein the solid-state image-sensing device has a plurality of second pixels.
4. (Original) A solid-state image-sensing device as claimed in claim 3, wherein the first pixels are arranged in a two-dimensional array, and the second pixels are arranged in a line in such a way as to correspond one to one to columns of the first pixels.
5. (Original) A solid-state image-sensing device as claimed in claim 4, further comprising:
a plurality of output signal lines provided one for each column of pixels, the output signal lines each permitting the output signals of the first and second pixels arranged in an identical column to be extracted therethrough.
6. (Original) A solid-state image-sensing device as claimed in claim 1, wherein the second pixel is smaller in size than the first pixel.
7. (Original) A solid-state image-sensing device as claimed in claim 1, wherein the first and second pixels have different circuit configurations.

8. (Original) A solid-state image-sensing device as claimed in claim 7, wherein, whereas the first pixel includes the photoelectric conversion element, the second pixel includes no photoelectric conversion element.

9. (Original) A solid-state image-sensing device as claimed in claim 1, wherein the first and second pixels have an identical circuit configuration.

10. (Original) A solid-state image-sensing device as claimed in claim 9, wherein the first and second pixels receive different voltages.

11. (Original) A solid-state image-sensing device as claimed in claim 1, wherein the first and second pixels each include a plurality of MOS transistors.

12. (Original) A solid-state image-sensing device as claimed in claim 1, wherein the first pixel generates selectively either the output signal that is logarithmically proportional to the amount of incident light or an output signal that is linearly proportional to the amount of incident light.

13. (Original) A solid-state image-sensing device as claimed in claim 1, further comprising:
a compensation circuit for compensating the output signal of the first pixel with the output signal of the second pixel.

14. (Original) A solid-state image-sensing device as claimed in claim 13, wherein the compensation circuit includes a storage circuit for storing the output signal of the second pixel and a differential amplifier circuit for outputting a difference between the output signal of the first pixel and the output signal of the second pixel stored in the storage circuit.

15. (Original) A solid-state image-sensing device comprising:
a first pixel including a photoelectric conversion element and capable of generating selectively either an output signal that is logarithmically proportional to an amount of light

incident on the photoelectric conversion element or an output signal that is linearly proportional to the amount of light incident on the photoelectric conversion element;

a second pixel for generating as an output signal a compensation signal with which to compensate the output signal of the first pixel; and

a reading circuit for reading out the output signals of the first and second pixels.

16. (Previously added) A solid-state image-sensing device comprising:

a first pixel, which includes a photoelectric conversion element, for generating a first pixel output signal that is logarithmically proportional to an amount of light incident on the photoelectric conversion element;

a second pixel for generating a second pixel output signal,

wherein the second pixel output signal is used for reducing signal noise that is caused by the first pixel; and

a reading circuit for reading out the output signals of the first and second pixels.

17. (Previously added) A solid-state image-sensing device as claimed in claim 16, further comprising a memory for storing the second pixel output signal.

18. (Previously added) A solid-state image-sensing device as claimed in claim 16, wherein the signal noise caused by the first pixel is a result of a switching action of at least one semiconductor device included therein.

19. (Previously added) A solid-state image-sensing device as claimed in claim 18, wherein the signal noise caused by the first pixel is a result of a transistor being turned off.

20. (Previously added) A solid-state image-sensing device as claimed in claim 16, wherein the signal noise caused by the first pixel is a result of the first pixel being reset.

21. (New) A solid-state image sensing device comprising:

a first pixel including a photoelectric conversion element and capable of generating

an output signal that is logarithmically proportional to an amount of light incident on the photoelectric conversion element;

a reading circuit for reading out the output signal of the first pixel; and

a second pixel for generating a compensation signal with which to compensate for a variation ascribable to a characteristic of the reading circuit.

22. (New) A solid-state image-sensing device as claimed in claim 21, wherein the characteristic of the reading circuit is an amplification factor thereof.

23. (New) A solid-state image-sensing device as claimed in claim 21, wherein the reading circuit is a transistor.
